M54HC574

RAD-HARD OCTAL D-TYPE FLIP FLOP WITH 3 STATE OUTPUT NON INVERTING

- **HIGH SPEED:**
  f_{MAX} = 90MHz (TYP.) at V_{CC} = 6V
- **LOW POWER DISSIPATION:**
  I_{CC} = 4µA(MAX.) at T_A=25°C
- **HIGH NOISE IMMUNITY:**
  V_{NIH} = V_{NIL} = 28% V_{CC} (MIN.)
- **SYMMETRICAL OUTPUT IMPEDANCE:**
  $|I_{OH}|$ = I_{OL} = 6mA (MIN)
- **BALANCED PROPAGATION DELAYS:**
  $t_{PLH} \cong t_{PHL}$
- **WIDE OPERATING VOLTAGE RANGE:**
  V_{CC} (OPR) = 2V to 6V
- **PIN AND FUNCTION COMPATIBLE WITH 54 SERIES 574**
- **SPACE GRADE-1: ESA SCC QUALIFIED**
- **50 krad QUALIFIED, 100 krad AVAILABLE ON REQUEST**
- **NO SEL UNDER HIGH LET HEAVY IONS IRRADIATION**
- **DEVICE FULLY COMPLIANT WITH SCC-9203-054**

DESCRIPTION

The M54HC574 is an high speed CMOS OCTAL D-TYPE FLIP FLOP WITH 3-STATE OUTPUTS INVERTING fabricated with sub-micron silicon gate C^2MOS technology.

This 8 bit D-TYPE FLIP FLOP is controlled by a clock input (CK) and an output enable input ($\overline{OE}$).

DILC-20   **FPC-20**
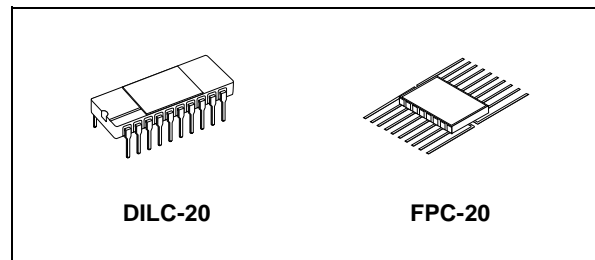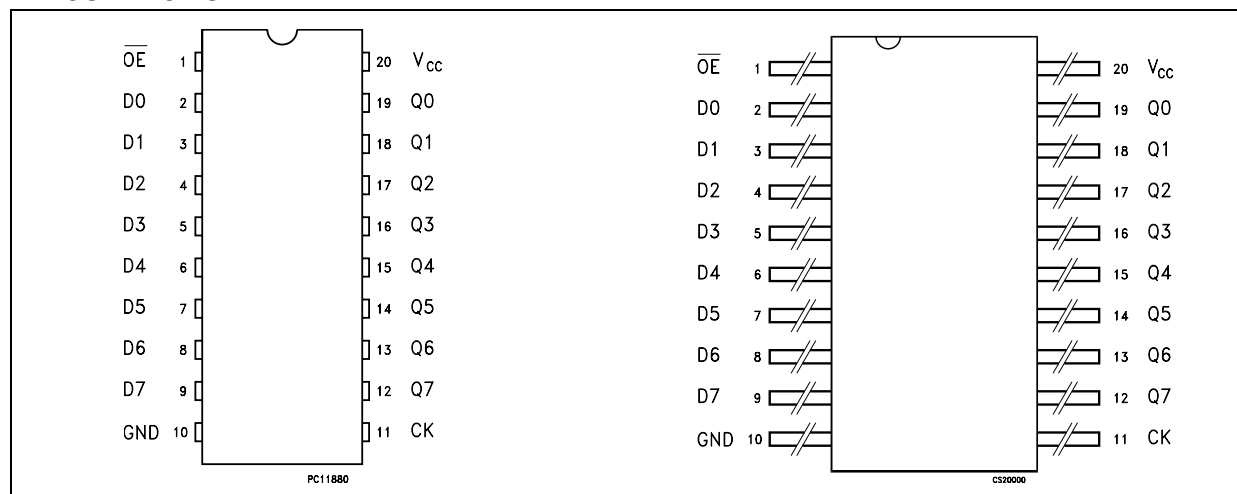
ORDER CODES

PACKAGE	FM	EM
DILC	M54HC574D	M54HC574D1
FPC	M54HC574K	M54HC574K1

On the positive transition of the clock, the Q outputs will be set to the logic state that were setup at the D inputs.

While the $\overline{OE}$ input is at low level, the eight outputs will be in a normal logic state (high or low logic level) and while $\overline{OE}$ is in high level the outputs will be in a high impedance state.

The output control does not affect the internal operation of flip-flops; that is, the old data can be retained or the new data can be entered even while the outputs are off.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.
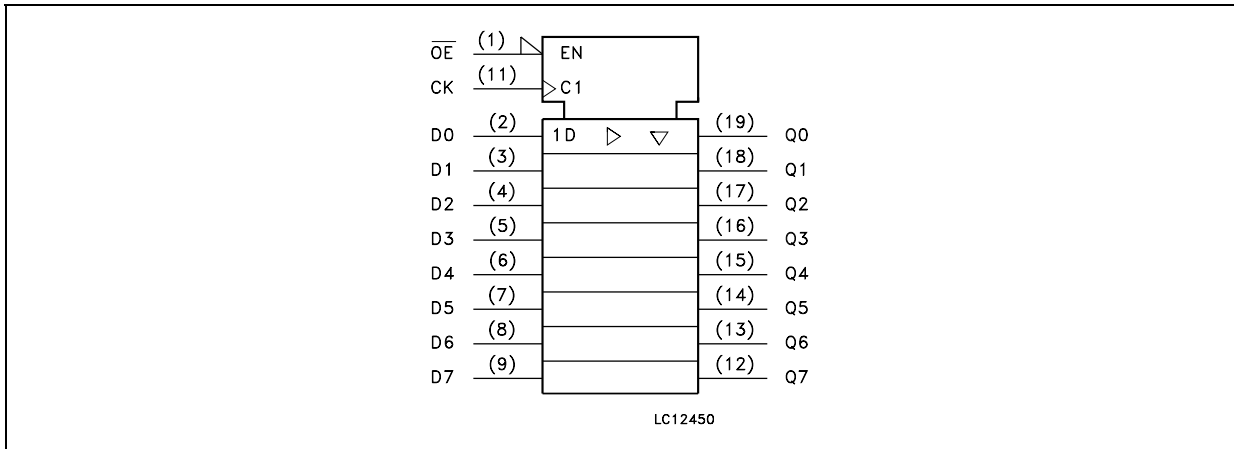
PIN CONNECTION

Figure 1: IEC Logic Symbols

LC12450

Figure 2: Input And Output Equivalent Circuit

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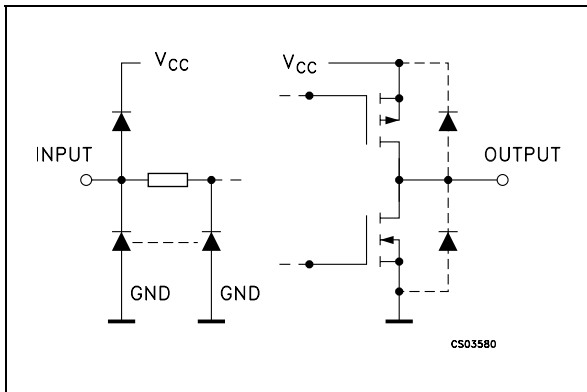
Table 1: Pin Description

PIN N°	SYMBOL	NAME AND FUNCTION
1	$\overline{OE}$	3 State Output Enable Input (Active LOW)
2, 3, 4, 5, 6, 7, 8, 9	D0 to D7	Data Inputs
12, 13, 14, 15, 16, 17, 18, 19	Q7 to Q0	3 State Outputs
11	CK	Clock Input (LOW to HIGH, edge triggered)
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

Table 2: Truth Table

INPUTS			OUTPUT
$\overline{OE}$	CK	D	Q
H	X	X	Z
L	⌐L	X	NO CHANGE
L	⌐↑	L	L
L	⌐↑	H	H

X: Don't Care
Z: High Impedance

Figure 3: Logic Diagram
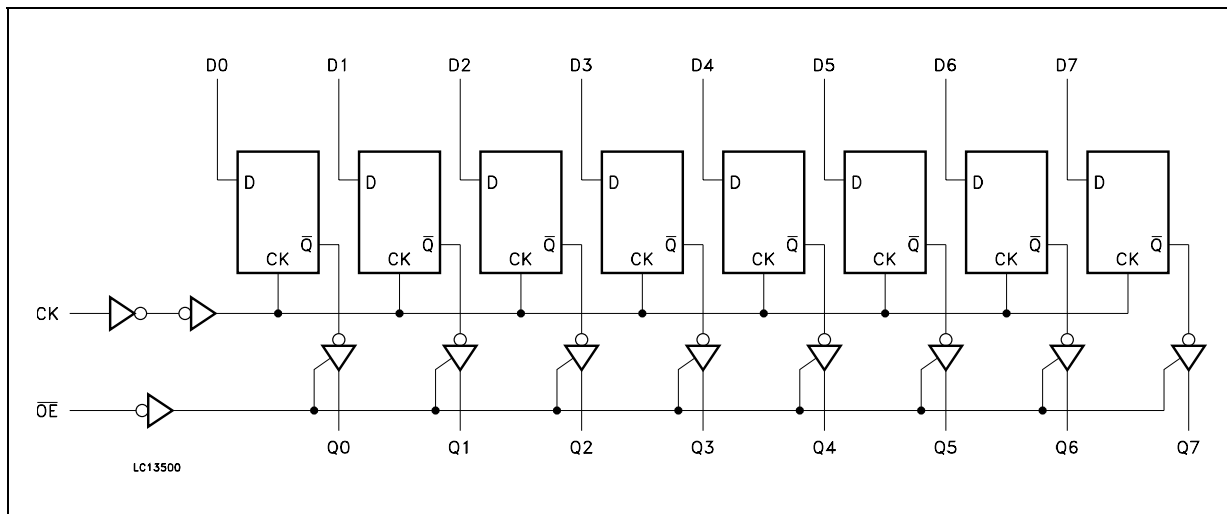
This logic diagram has not be used to estimate propagation delays

Table 3: Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	420	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	265	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

Table 4: Recommended Operating Conditions

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature		-55 to 125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2.0V	0 to 1000	ns
		V_{CC} = 4.5V	0 to 500	ns
		V_{CC} = 6.0V	0 to 400	ns

Table 5: DC Specifications

Symbol	Parameter	Test Condition		$T_A = 25°C$			-40 to 85°C		-55 to 125°C		Unit
		V_{CC} (V)		Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5	I_O=-20 µA	4.4	4.5		4.4		4.4		
		6.0	I_O=-20 µA	5.9	6.0		5.9		5.9		
		4.5	I_O=-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I_O=-7.8 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	I_O=20 µA		0.0	0.1		0.1		0.1	V
		4.5	I_O=20 µA		0.0	0.1		0.1		0.1	
		6.0	I_O=20 µA		0.0	0.1		0.1		0.1	
		4.5	I_O=6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I_O=7.8 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	µA
I_{OZ}	High Impedance Output Leakage Current	6.0	$V_I = V_{IH}$ or V_{IL} $V_O = V_{CC}$ or GND			± 0.5		± 5		± 10	µA
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	µA

Table 6: AC Electrical Characteristics (C_L = 50 pF, Input t_r = t_f = 6ns)

Symbol	Parameter	Test Condition V_{CC} (V)	Test Condition C_L (pF)	Test Condition	T_A = 25°C Min.	T_A = 25°C Typ.	T_A = 25°C Max.	-40 to 85°C Min.	-40 to 85°C Max.	-55 to 125°C Min.	-55 to 125°C Max.	Unit
t_{TLH} t_{THL}	Output Transition Time	2.0				25	60		75		90	
		4.5	50			7	12		15		18	ns
		6.0				6	10		13		15	
t_{PLH} t_{PHL}	Propagation Delay Time (CK - Q)	2.0				70	150		190		225	
		4.5	50			20	30		38		45	ns
		6.0				15	26		32		38	
		2.0				88	190		240		285	
		4.5	150			25	38		48		57	ns
		6.0				19	32		41		48	
t_{PZL} t_{PZH}	High Impedance Output Enable Time	2.0		R_L = 1 KΩ		48	125		155		190	
		4.5	50	R_L = 1 KΩ		15	25		31		38	ns
		6.0		R_L = 1 KΩ		12	21		26		32	
		2.0		R_L = 1 KΩ		60	165		205		250	
		4.5	150	R_L = 1 KΩ		20	33		41		50	ns
		6.0		R_L = 1 KΩ		16	28		35		43	
t_{PLZ} t_{PHZ}	High Impedance Output Disable Time	2.0		R_L = 1 KΩ		34	125		155		190	
		4.5	50	R_L = 1 KΩ		17	25		31		38	ns
		6.0		R_L = 1 KΩ		15	21		26		32	
f_{MAX}	Maximum Clock Frequency	2.0			6.2	18		5		4.2		
		4.5	50		31	75		25		21		MHz
		6.0			37	90		30		25		
$t_{W(L)}$ $t_{W(H)}$	Minimum Pulse Width (CLOCK)	2.0				15	75		95		110	
		4.5	50			6	15		19		22	ns
		6.0				6	13		16		19	
t_s	Minimum Set-up Time	2.0				25	75		95		110	
		4.5	50			6	15		19		22	ns
		6.0				4	13		16		19	
t_h	Minimum Hold Time	2.0					0		0		0	
		4.5	50				0		0		0	ns
		6.0					0		0		0	

Table 7: Capacitive Characteristics

Symbol	Parameter	Test Condition V_{CC} (V)	Test Condition	T_A = 25°C Min.	T_A = 25°C Typ.	T_A = 25°C Max.	-40 to 85°C Min.	-40 to 85°C Max.	-55 to 125°C Min.	-55 to 125°C Max.	Unit
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{OUT}	Output Capacitance				10						pF
C_{PD}	Power Dissipation Capacitance (note 1)				54						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

Figure 4: Test Circuit
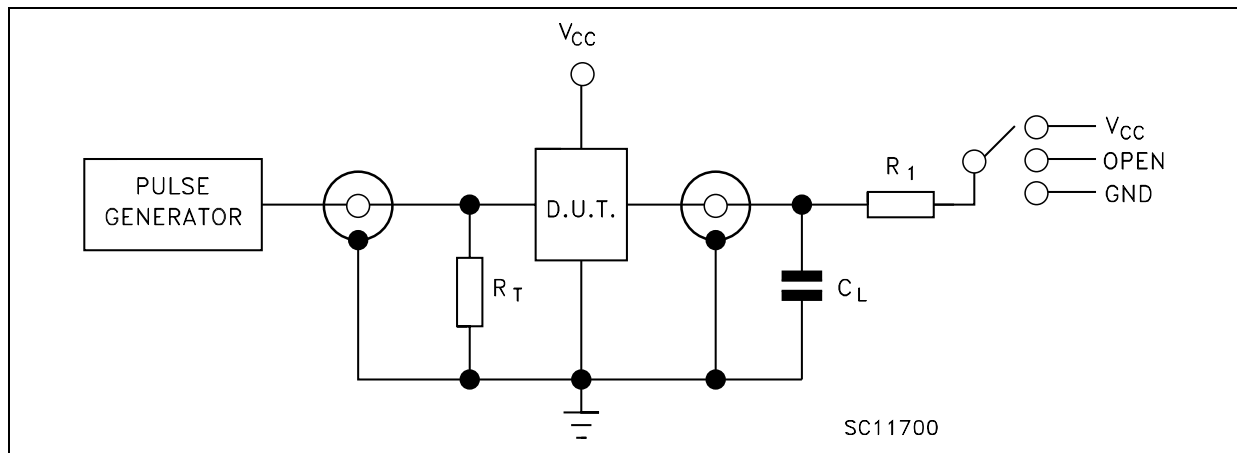
TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	V_{CC}
t_{PZH}, t_{PHZ}	GND

C_L = 50pF/150pF or equivalent (includes jig and probe capacitance)
R_1 = 1KΩ or equivalent
R_T = Z_{OUT} of pulse generator (typically 50Ω)

Figure 5: Waveform - CK To Qn Propagation Delays, CK Maximum Frequency, Dn To CK Setup And Hold Times (f=1MHz; 50% duty cycle)
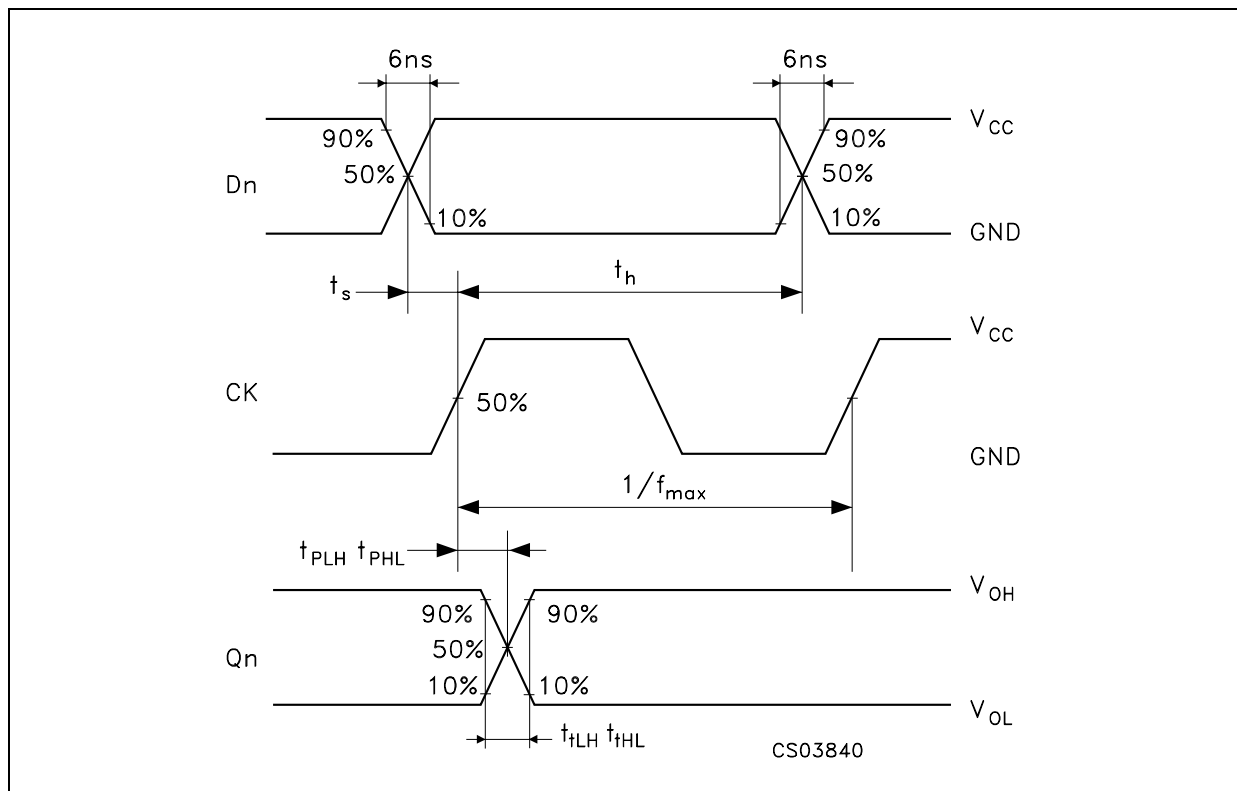
Figure 6: Waveform - Output Enable And Disable Times (f=1MHz; 50% duty cycle)

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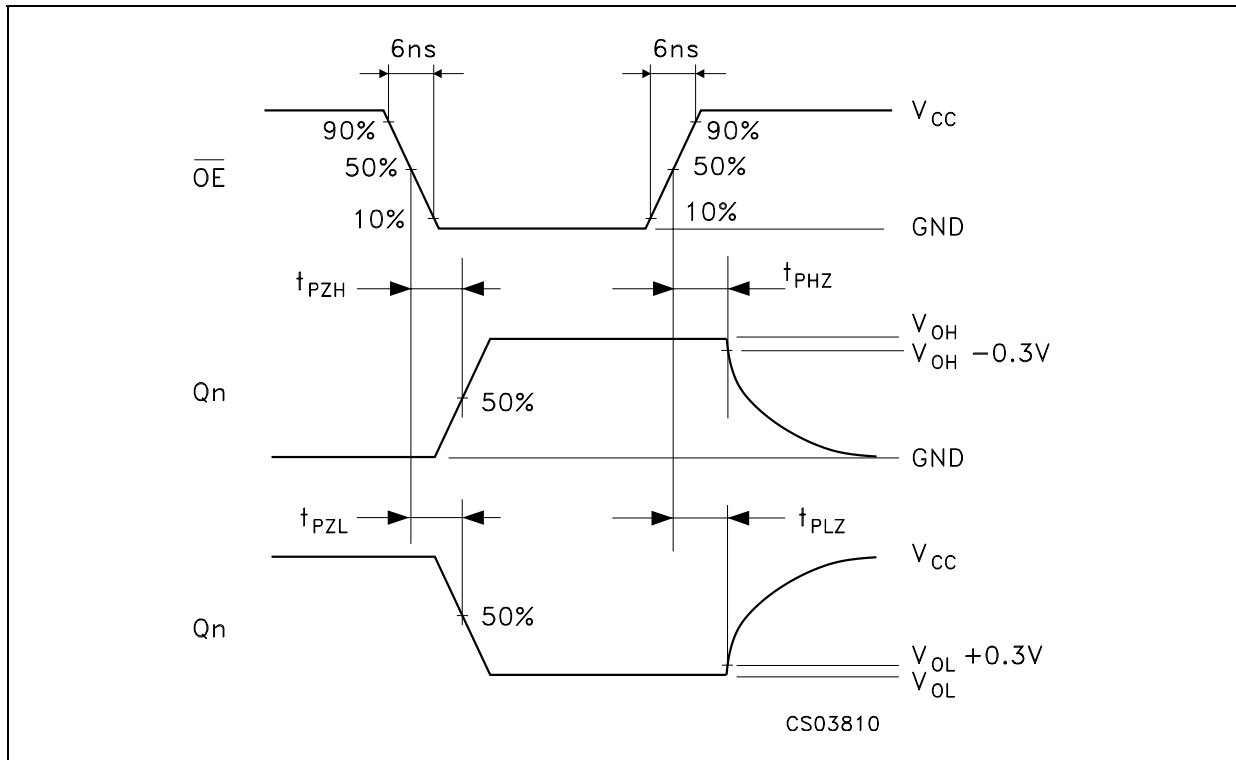
Figure 7: Waveform - CK Minimum Pulse Width (f=1MHz; 50% duty cycle)

CS03830
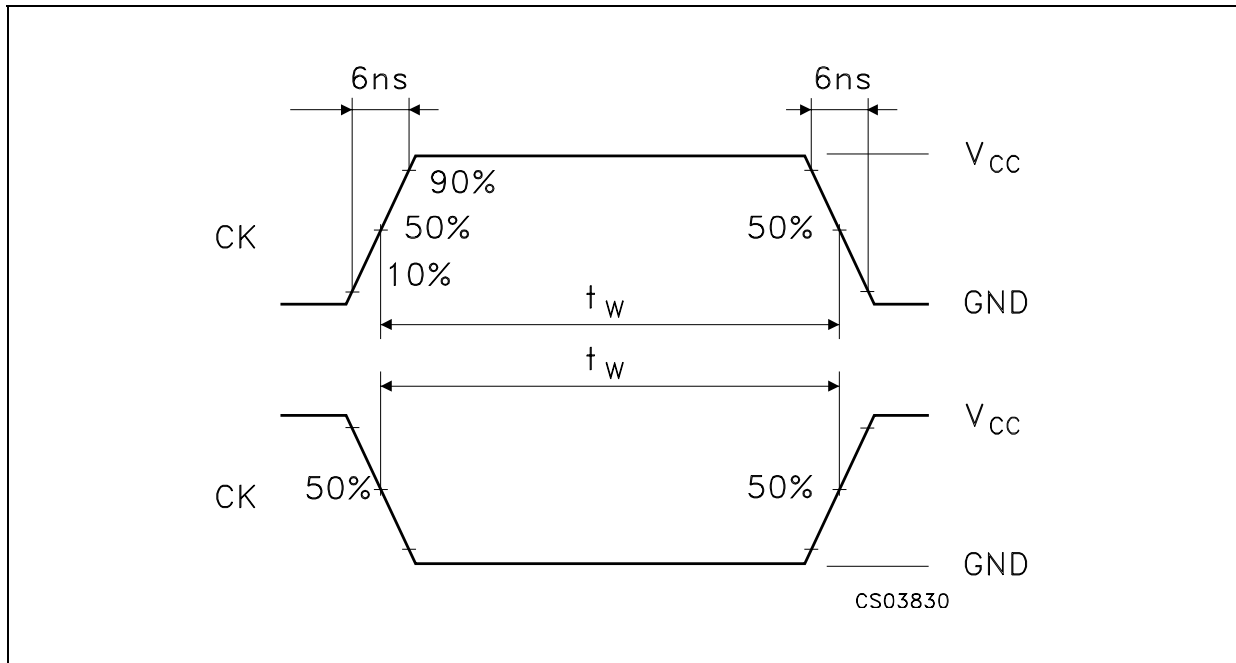
DILC-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.1		2.71	0.083		0.107
a1	3.00		3.70	0.118		0.146
a2	0.63	0.88	1.14	0.025	0.035	0.045
B	1.93	2.03	2.23	0.076	0.080	0.088
b	0.40	0.45	0.50	0.016	0.018	0.020
b1	0.20	0.254	0.30	0.008	0.010	0.012
D	25.14	25.40	25.65	0.990	1.000	1.010
E	7.36	7.62	7.87	0.290	0.300	0.310
e		2.54			0.100	
e1	22.73	22.86	22.99	0.895	0.900	0.905
e2	7.62	7.87	8.12	0.300	0.310	0.320
F	7.29	7.49	7.70	0.287	0.295	0.303
I			3.86			0.152
K	11.30		11.56	0.445		0.455
L	1.14	1.27	1.40	0.045	0.050	0.055
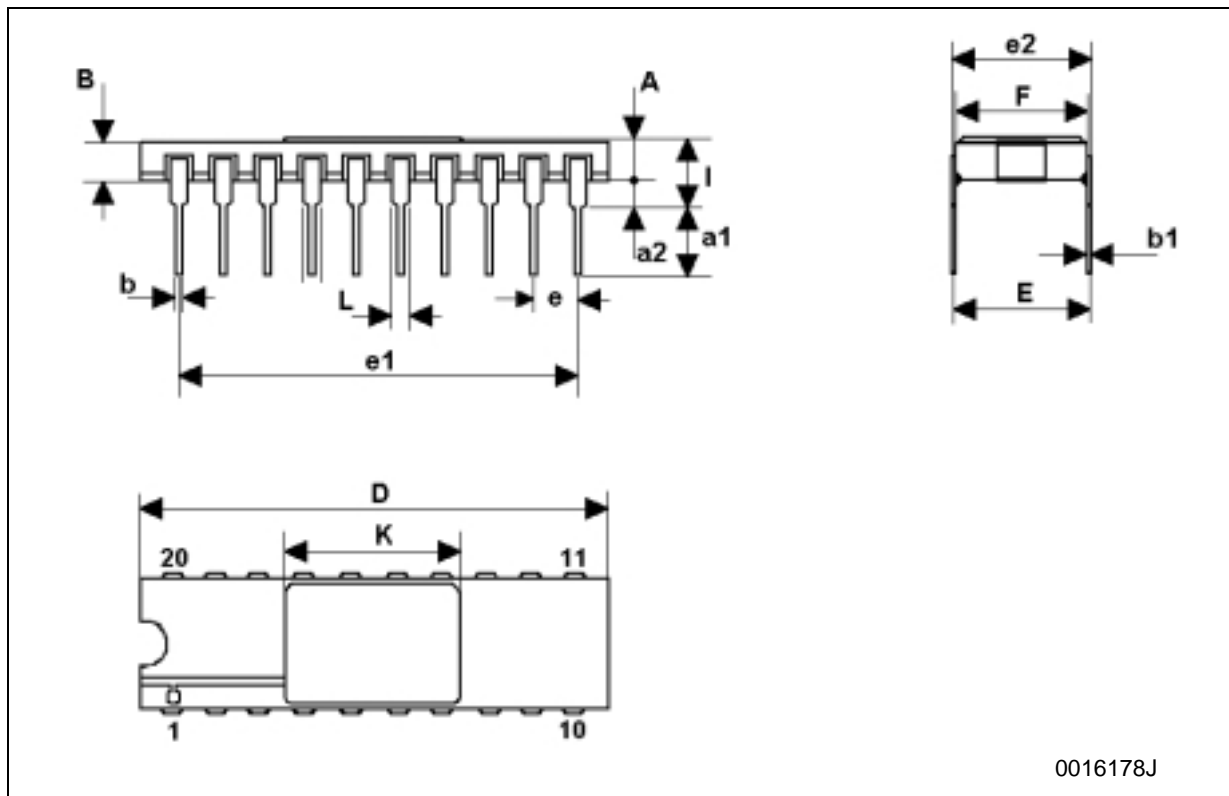
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FPC-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	9.98	10.16	10.34	0.393	0.400	0.407
B	9.98	10.16	10.34	0.393	0.400	0.407
C	1.45	1.61	1.78	0.57	0.63	0.070
D	0.10	0.127	0.18	0.004	0.005	0.007
E	11.30	11.43	11.56	0.445	0.450	0.455
F		1.27			0.050	
G	0.38	0.43	0.48	0.015	0.017	0.019
H	7.24		8.16	0.285		0.320
L	24.46		26.67	0.960		1.050
M	0.45	0.50	0.55	0.018	0.020	0.022
N		7.87			0.310	
O	1.14	1.27	1.40	0.045	0.050	0.055
P	0.10	0.18	0.25	0.004	0.007	0.010

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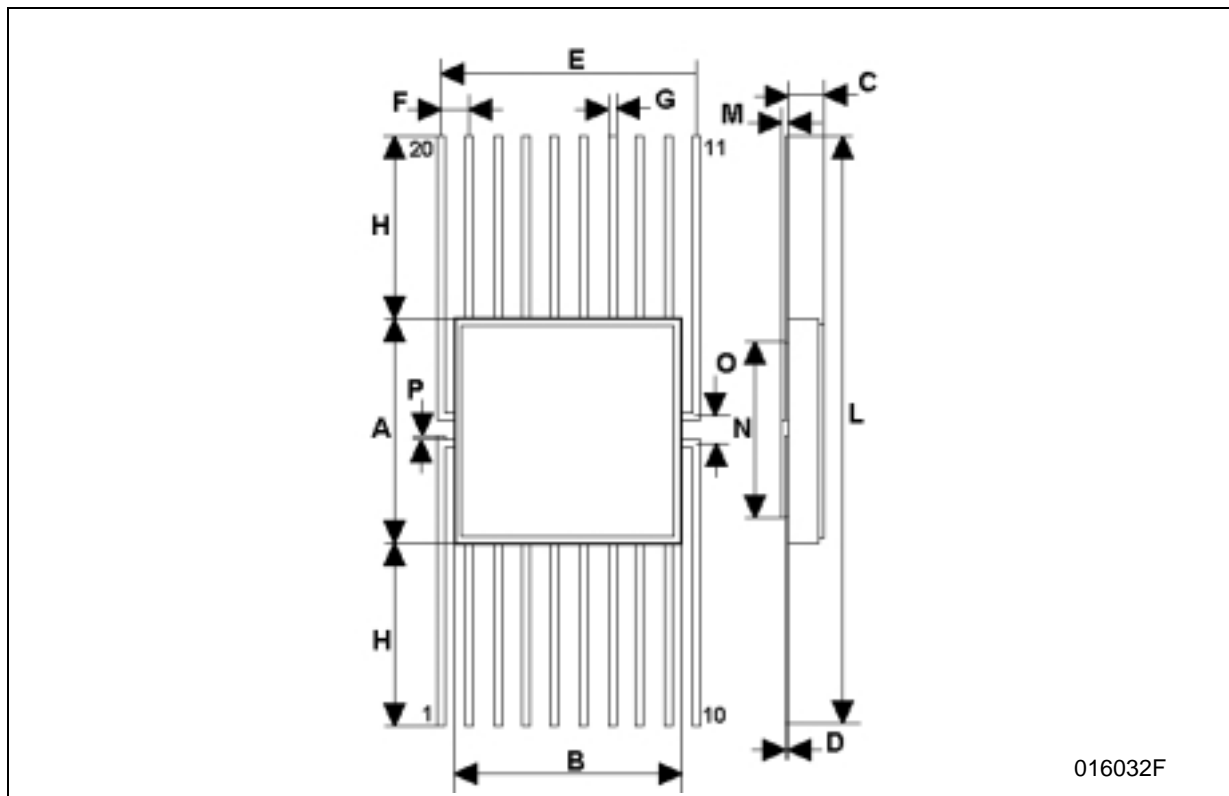
Table 8: Revision History

Date	Revision	Description of Changes
01-Jun-2004	1	First Release